

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application Serial No. .... 10/636,038  
Confirmation No. .... 9972  
Filing Date ..... August 6, 2003  
Inventor..... Gurtej S. Sandhu  
Assignee..... Micron Technology, Inc.  
Group Art Unit..... 1762  
Examiner ..... Fuller, Eric B.  
Attorney's Docket No. .... MI22-2194  
Customer No. .... 021567  
Title: Methods of Forming Material on a Substrate, and Method of Forming a  
Field Effect Transistor Gate Oxide on a Substrate

**RESPONSE TO JUNE 20, 2006 OFFICE ACTION**

To: Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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**AMENDMENTS**

In response to the Office Action of June 20, 2006, applicant amends and remarks as follows.